TOSHIBA Transistor Silicon-Germanium NPN Epitaxial Planer Type

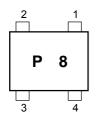
MT4S102T

UHF-SHF Low Noise Amplifier Application

FEATURES

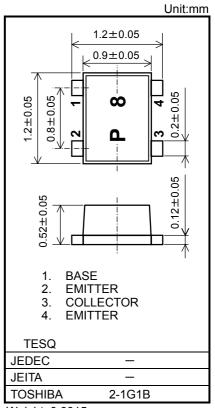
- Low Noise Figure :NF=0.58dB (@f=2GHz)
- High Gain:|S21e|²=16.0dB (@f=2GHz)

Marking



Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-Base voltage	V _{CBO}	6	V
Collector-Emitter voltage	V _{CEO}	3	V
Emitter-Base voltage	V _{EBO}	1.2	V
Collector-Current	Ι _C	20	mA
Base-Current	Ι _Β	10	mA
Collector Power dissipation	PC	60	mW
Junction temperature	Tj	150	°C
Storage temperature Range	T _{stg}	-55~150	°C



Weight: 0.0015 g

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition Frequency	f _T	V _{CE} =2V, I _C =15mA, f=2GHz	21	25	_	GHz
Insertion Gain	S21e ² (1)	V _{CE} =2V, I _C =15mA, f=2GHz	13.5	16.0	_	dB
	S21e ² (2)	V _{CE} =2V, I _C =15mA, f=5.2GHz	_	9.0	_	dB
Noise Figure	NF(1)	V _{CE} =2V, I _C =10mA, f=2GHz	_	0.58	0.85	dB
	NF(2)	V _{CE} =2V, I _C =10mA, f=5.2GHz	_	1.4	_	dB

Electrical Characteristics (Ta = 25°C)

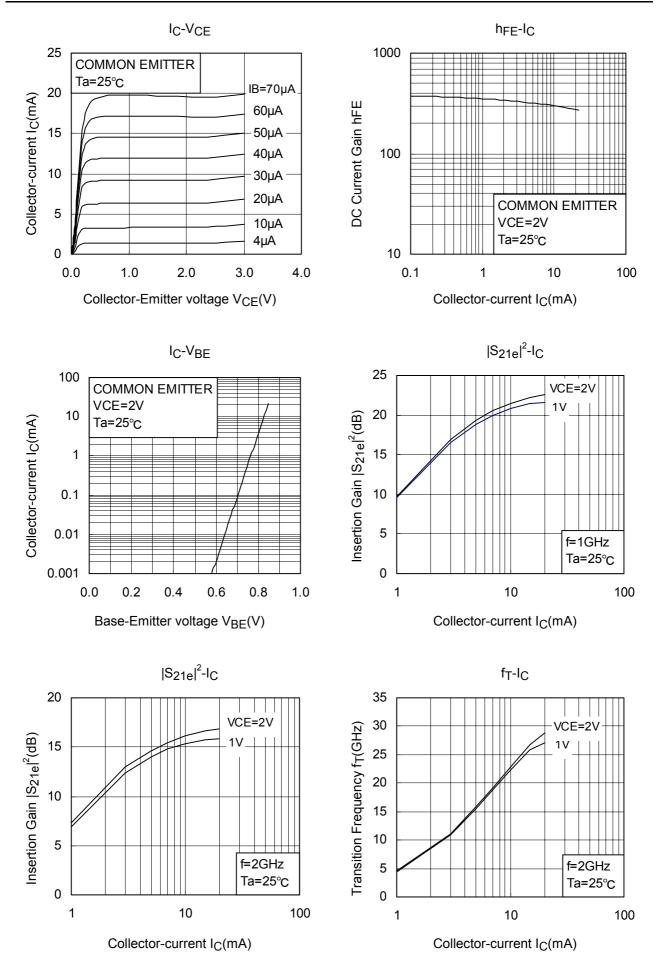
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector Cut-off Current	I _{CBO}	V _{CB} =6V, I _E =0	_	_	1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =1V, I _C =0	_	_	1	μA
DC Current Gain	hFE	V _{CE} =2V, I _C =15mA	200	_	400	-
Output Capacitance	C _{ob}	V _{CB} =2V, I _E =0, f=1MHz	_	0.43	0.6	pF
Reverse Transfer Capacitance	C _{re}	V _{CB} =2V, I _E =0, f=1MHz (Note 1)	_	0.17	0.25	pF

Note 1: Cre is measured by 3 terminal method with capacitance bridge.

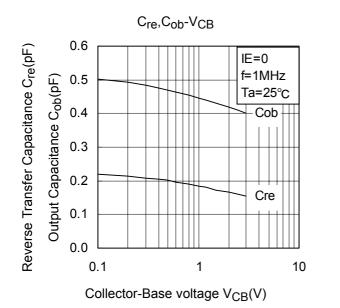
Caution: This device is sensitive to electrostatic discharge.

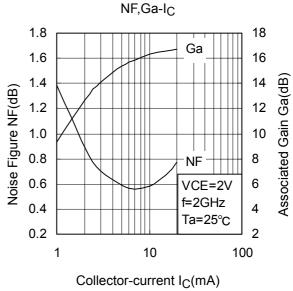
Please make enough tool and equipment earthed when you handle.

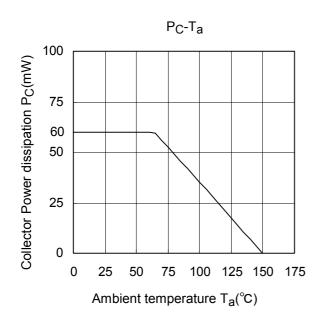
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Handbook" etc.,

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